

# MS 23 P 21

### P-Channel 20-V (D-S) MOSFET

### **Description**

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low RDS(on) and to ensure minimal power loss and heat dissipation.

Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

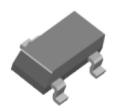
#### Features

- Low rDS(on) provides higher efficiency and extends battery life
- Low thermal impedance copper lead frame SOT-23 saves board space
- Fast switching speed
- · High performance trench technology
- RoHS compliant package

Package type: SOT-23

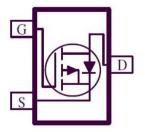
### **Packing & Order Information**

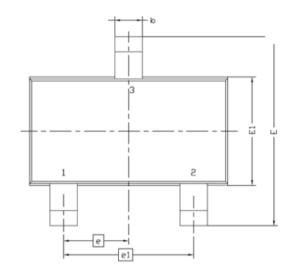
3,000/Reel

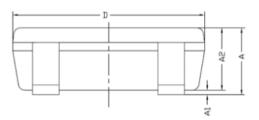


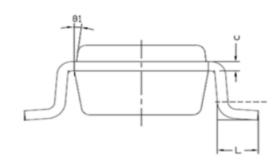


Graphic symbol









Symbol	MILLIMETERS			
Symbol	MIN	MAX		
Α	8.0	1.2		
A1	0	0.1		
A2	0.7	1.1		
b	0.3	0.5		
С	0.1	0.2		
D	2.7	3.1		
Е	2.6	3		
E1	1.4	1.8		
е	0.95 BSC			
e1	1.9 BSC			
L	0.3	0.6		
θ1	7° NOM			



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### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)					
Symbol	Parameter	Value	Unit		
$V_{DS}$	Drain-Source Voltage	-20	V		
$V_{GS}$	Gate-Source Voltage	±8	V		
$I_{\mathrm{D}}$	Continuous Drain Current <sup>a</sup> (T <sub>A</sub> =25°C)	-4.1	A		
$I_{DM}$	Pulsed Drain Current <sup>b</sup>	-10	A		
$I_S$	Continuous Source Current (Diode Conduction) <sup>a</sup>	0.46	A		
$T_{\rm J}, T_{ m STG}$	Operating Junction and Storage Temperature	-55 to +150	°C		
Pd	Power Dissipation@ TC=25°C	1.25	W		

#### NOTE:

1. Repetitive rating; pulse width limited by maximum junction temperature.

Thermal Characteristics (Tc=25°C unless otherwise specified)					
Parameter	Symbol	Value	Units		
Maximum Junction-to-Case	RөдС	150	OCAN.		
Maximum Junction-to-Ambient	R <sub>θJA</sub>	100	°C/W		

Static						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
$V_{GS(th)}$	Gate-Threshold Voltage	$V_{DS}=V_{GS},I_D\!=\text{-250}\mu\text{A}$	-0.4		-1.5	V
$I_{GSS}$	Gate-Body Leakage	$V_{DS} = 0 V$ , $V_{GS} = \pm 8 V$			±100	nA
I <sub>DS S</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 \ V \ , \ V_{GS} = 0 \ V$ $V_{DS} = -16 \ V \ , \ V_{GS} = 0 \ V \ , \ T_J = 55 ^{\circ} C$			-1 -10	uA
I <sub>D(on)</sub>	On-State Drain Current <sup>A</sup>	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-5			A
rDS (on)	Drain-Source On-Resistance <sup>A</sup>	V <sub>DS</sub> = -4.5 V, I <sub>D</sub> = -4.1 A V <sub>DS</sub> = -2.5 V, I <sub>D</sub> = -3.2 A			79 110	mΩ
gfs	Forward Tranconductance <sup>A</sup>	$V_{DS} = -5 \text{ V}, V_{GS} = -1.25 \text{ V}$		9		S
V <sub>SD</sub>	Diode Forward Voltage	$I_S = -0.46 \text{ V}, I_D = 0 \text{ V}$		-0.65		V
I <sub>SM</sub>	Pulsed Body-Diode Current <sup>C</sup>				-10	A



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Dyna mic <sup>b</sup>						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$Q_g$	Total Gate Charge	$V_{DS} = -10 \text{ V}$ , $I_{D}$ =-4.1 A, $V_{GS} = -4.5 \text{ V}$		7.2		nC
$Q_{gs}$	Gate-Source Charge			1.7		nC
$Q_{\rm gd}$	Gate-Drain Charge			1.5		nC
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \text{ IL} = -1 \text{ A}, \\ V_{GEN} = -4.5 \text{ V}, \text{ R}_{G} = 6 \Omega$		10		ns
$t_{\rm r}$	Rise Time			9		ns
$t_{d(\rm off)} \\$	Turn-Off Delay Time			27		ns
tf	Fall Time			11		ns
Ciss	Input Capacitance	P-Channel $V_{DS} = -15 \text{ V}$ $I_D = -3.7 \text{ A}, V_{GS} = 0 \text{ V}$		500		nC
Coss	Output Capacitance			90		nC
C <sub>RSS</sub>	Reverse Transfer Capacitance			60		nC

#### Notes:

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Repetitive rating, pulse width limited by junction temperature.



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